

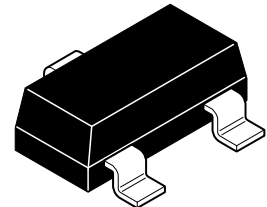


ZXMN6A07F

60V SOT23 N-channel enhancement mode mosfet

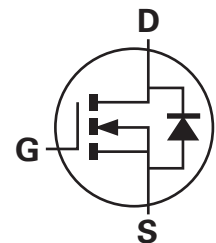
Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.250 @ $V_{GS} = 10V$	1.4
	0.350 @ $V_{GS} = 4.5V$	1.2



Description

This new generation trench MOSFET from Zetex utilizes a unique structure combining the benefits of low on-state resistance with fast switching speed.

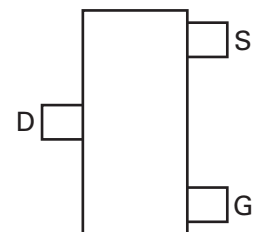


Features

- Low on-resistance
- Fast switching speed
- Low threshold
- SOT23 package

Applications

- DC-DC converters
- Power management functions
- Relay and solenoid driving
- Motor control



Top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A07FTA	7	8	3,000

Device marking

7N6



Absolute maximum ratings

ZXMN6A07F

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DSS}	60	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current @ $V_{GS} = 10V$; $T_{amb} = 25^{\circ}C^{(b)}$	I_D	1.4	A
@ $V_{GS} = 10V$; $T_{amb} = 70^{\circ}C^{(b)}$		1.1	
@ $V_{GS} = 10V$; $T_{amb} = 25^{\circ}C^{(a)}$		1.2	
Pulsed drain current ^(c)	I_{DM}	6.9	A
Continuous source current (body diode) ^(b)	I_S	1	A
Pulsed source current (body diode) ^(c)	I_{SM}	6.9	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P_D	625	mW
Linear derating factor		5	mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P_D	806	mW
Linear derating factor		6.4	mW/ $^{\circ}C$
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient	$R_{\theta JA}$	200	$^{\circ}C/W$
Junction to ambient	$R_{\theta JA}$	155	$^{\circ}C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ sec.
- (c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

ZXMN6A07F

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	60			V	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero gate voltage drain current	I_{DSS}			1	μA	$V_{DS} = 60\text{V}$, $V_{GS} = 0\text{V}$
Gate-body leakage	I_{GSS}			100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0		3.0	V	$I_D = 250\mu\text{A}$, $V_{DS} = V_{GS}$
Static drain-source on-state resistance ^(*)	$R_{DS(on)}$			0.250	Ω	$V_{GS} = 10\text{V}$, $I_D = 1.8\text{A}$
				0.350	Ω	$V_{GS} = 4.5\text{V}$, $I_D = 1.3\text{A}$
Forward transconductance ^{(*)(‡)}	g_{fs}		2.3		S	$V_{DS} = 15\text{V}$, $I_D = 1.8\text{A}$
Dynamic^(‡)						
Input capacitance	C_{iss}		166		pF	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	C_{oss}		19.5		pF	
Reverse transfer capacitance	C_{rss}		8.7		pF	
Switching^(†) (‡)						
Turn-on-delay time	$t_{d(on)}$		1.8		ns	$V_{DD} = 30\text{V}$, $V_{GS} = 10\text{V}$ $I_D = 1.8\text{A}$ $R_G \approx 6.0\Omega$
Rise time	t_r		1.4		ns	
Turn-off delay time	$t_{d(off)}$		4.9		ns	
Fall time	t_f		2.0		ns	
Total gate charge	Q_g		1.65			$V_{DS} = 30\text{V}$, $V_{GS} = 5\text{V}$ $I_D = 1.8\text{A}$
Total gate charge	Q_g		3.2		nC	$V_{DS} = 30\text{V}$, $V_{GS} = 10\text{V}$ $I_D = 1.8\text{A}$
Gate-source charge	Q_{gs}		0.67		nC	
Gate drain charge	Q_{gd}		0.82		nC	
Source-drain diode						
Diode forward voltage ^(*)	V_{SD}		0.80	0.95	V	$T_j = 25^{\circ}\text{C}$, $I_S = 0.45\text{A}$, $V_{GS} = 0\text{V}$
Reverse recovery time ^(‡)	t_{rr}		20.5		ns	$T_j = 25^{\circ}\text{C}$, $I_F = 1.8\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge ^(‡)	Q_{rr}		21.3		nC	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.